Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	77	((gate with (damascene inlaid "in-laid")) same (metal iridium ir niobium nb platinum pt rhenium re rhodium rh tantalum ta tan tasin tungsten w vanadium v)) same barrier	US-PGPUB; USPAT	OR	ON	2005/03/16 14:32
L2	17	(((tungsten wolfram) with (carbonyl (carbon adj monoxide))) "w(co).sub.6") and (\$6cvd (chemical\$5 adj vapor))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 14:44
L3	85	(((tungsten wolfram) with (carbonyl (carbon adj monoxide))) "w(co).sub.6") same (\$6cvd (chemical\$5 adj vapor))	US-PGPUB; USPAT	OR	ON	2005/03/16 15:03
L4	123	((gate with (replacement dummy sacrificial)) same (metal iridium ir niobium nb platinum pt rhenium re rhodium rh tantalum ta tan tasin tungsten w vanadium v)) same barrier	US-PGPUB; USPAT	OR	ON	2005/03/16 15:06
L5	320	(gate with (damascene inlaid "in-laid")) and (gate with (replacement dummy sacrificial))	US-PGPUB; USPAT	OR	ON	2005/03/16 15:25
L6	1	"6586288".URPN.	USPAT	OR	OFF	2005/03/16 16:04
L7	49	(gate with (damascene inlaid "in-laid")) and ((gate with (replacement dummy sacrificial)))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 16:05
L8	39	((gate with (damascene inlaid "in-laid")) ((gate with (replacement dummy sacrificial)))) and ((metal iridium ir niobium nb platinum pt rhenium re rhodium rh tantalum ta tan tasin tungsten w vanadium v) same (barrier adhesion adherence))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/16 16:10
L9	199	(438/259.ccls. 438/270.ccls. 438/589.ccls. 438/592.ccls. 438/595.ccls. 438/926.ccls. 257/412.ccls. 257/751.ccls. 257/753.ccls.) and ((gate with (replacement dummy sacrificial)) same (metal iridium ir niobium nb platinum pt rhenium re rhodium rh tantalum ta tan tasin tungsten w vanadium v))	US-PGPUB; USPAT	OR	ON	2005/03/16 16:11

L10	147	(438/259.ccls. 438/270.ccls. 438/589.ccls. 438/592.ccls. 438/595.ccls. 438/926.ccls. 257/412.ccls. 257/751.ccls. 257/753.ccls.) and (gate with (damascene inlaid "in-laid"))	US-PGPUB; USPAT	OR	ON	2005/03/16 16:20
L11	9	((tft (thin adj film adj transistor)) same (soi sos "silicon on insulator" "silicon-on-insulator" "silicon on sapphire" "silicon-on-sapphire") same (polysilicon ((polycrystalline amorphous) adj silicon) crystalli\$10 recrystalli\$10) same (gate with (metal tungsten molybdenum aluminum copper platinum iridium rhenium rhodium ruthenium tantalum vanadium))) same (barrier adhesion adherence)	US-PGPUB; USPAT	OR	ON	2005/03/16 16:25
L12	476	(438/259.ccls. 438/270.ccls. 438/589.ccls. 438/592.ccls. 438/595.ccls. 438/926.ccls. 257/412.ccls. 257/751.ccls. 257/753.ccls.) and (gate with (replacement dummy sacrificial))	US-PGPUB; USPAT	OR	ON	2005/03/16 16:26